General Purpose Transistor

NPN Silicon

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	25	Vdc
Collector-Base Voltage	V _{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	I _C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

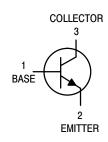
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM

STYLE 6



ZC = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary
depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT4124LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•	•	•	
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mAdc, I _E = 0)	V _(BR) CEO	25	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _(BR) CBO	30	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0)	Ісво	-	50	nAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	50	nAdc
ON CHARACTERISTICS	-	1	•	
DC Current Gain (Note 3) $ (I_C = 2.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) $ $ (I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) $	h _{FE}	120 60	360 -	-
Collector – Emitter Saturation Voltage (Note 3) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	-	0.3	Vdc
Base – Emitter Saturation Voltage (Note 3) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{BE(sat)}	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS		•	•	
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	300	_	MHz
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	8.0	pF
Collector-Base Capacitance (I _E = 0, V _{CB} = 5.0 V, f = 1.0 MHz)	C _{cb}	-	4.0	pF
Small–Signal Current Gain (I _C = 2.0 mAdc, V _{CE} = 10 Vdc, R _S = 10 k Ω , f = 1.0 kHz)	h _{fe}	120	480	-
Current Gain – High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz) (I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	h _{fe}	3.0 120	_ 480	-
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF	-	5.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle = 2.0%.

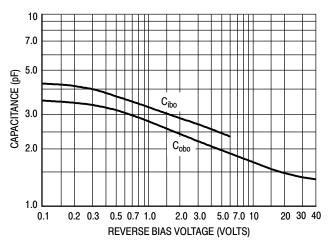


Figure 1. Capacitance

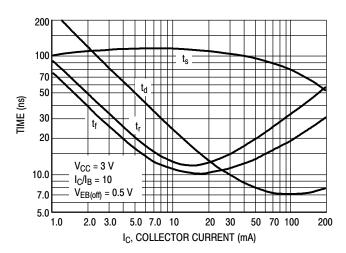


Figure 2. Switching Times

AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $(V_{CE} = 5 \text{ Vdc}, T_A = 25^{\circ}\text{C})$ Bandwidth = 1.0 Hz

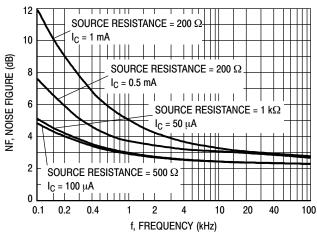


Figure 3. Frequency Variations

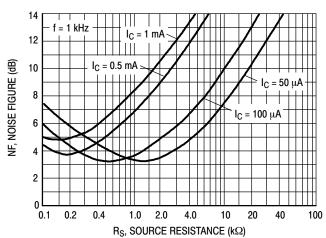
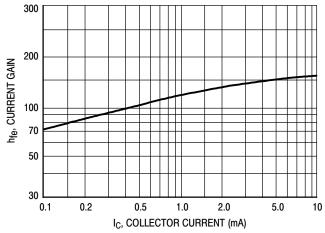


Figure 4. Source Resistance

h PARAMETERS

 $(V_{CE} = 10 \text{ V, f} = 1 \text{ kHz, } T_A = 25^{\circ}C)$



100

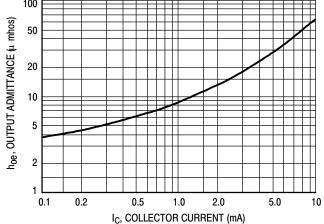
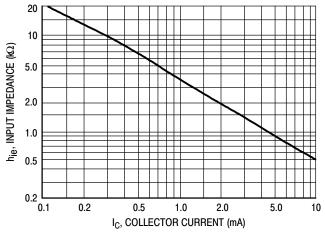


Figure 5. Current Gain

Figure 6. Output Admittance



10 h_{re} , VOLTAGE FEEDBACK RATIO (X 10-4) 7.0 5.0 3.0 2.0 1.0 0.7 0.5 0.1 0.2 0.5 1.0 2.0 5.0 10 I_C, COLLECTOR CURRENT (mA)

Figure 7. Input Impedance

Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

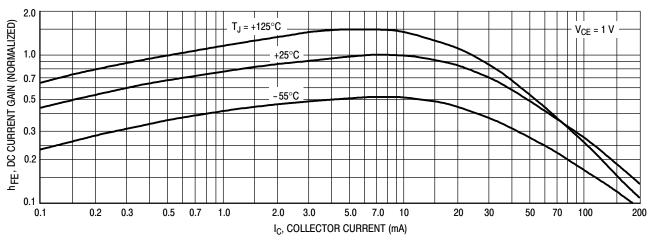


Figure 9. DC Current Gain

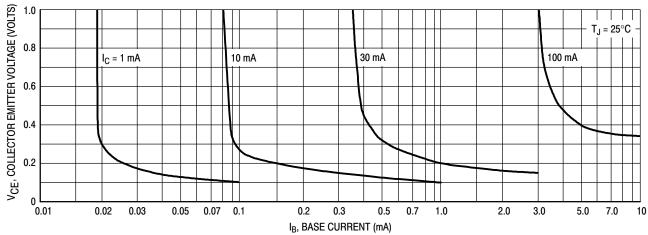


Figure 10. Collector Saturation Region

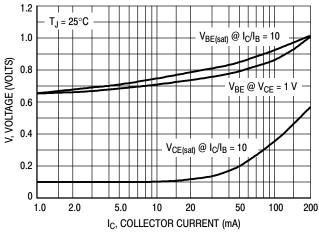


Figure 11. "On" Voltages

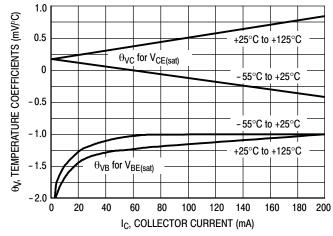


Figure 12. Temperature Coefficients

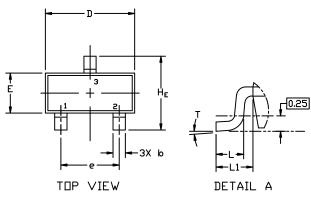




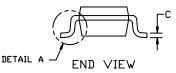
SOT-23 (TO-236) **CASE 318 ISSUE AT**

DATE 01 MAR 2023









NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
n	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
Ą	1.78	1.90	2.04	0.070	0.075	0.080
Г	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10°





XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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